Amendments to the Specification:

On page 1, after the title "PHOSPHORUS-CONTAINING SILAZANE COMPOSITION, PHOSPHORUS-CONTAINING SILICEOUS FILM, PHOSPHORUS-CONTAINING SILICEOUS FILLER, METHOD FOR PRODUCING PHOSPHORUS-CONTAINING SILICEOUS FILM, AND SEMICONDUCTOR DEVICE", please insert the following:

This application is a United States National Stage Patent Application under 35 U.S.C. § 371 of International Patent Application No. PCT/JP2004/009649, filed July 7, 2004, which claims priority to Japanese Patent Application No. 2003-199363, filed July 18, 2003.

On page 27, please replace paragraph [0073] with the following replacement paragraph:

[0073] Reference Example 2 [Synthesis of polymethylsilazane (2)]

Polymethylsilazane (about 370 g) was synthesized in the same manner as in Reference Example 1, except that, instead of 780 g of methyltrichlorosilane, a mixture of 720 g of methyltrichlorosilane (about 4.8 mol) with 65 g of dimethyldichlorosilane (about 0.5 mol) (methyltrichlorosilane : dimethyldichlorosilane = 95 : 10 (mol/mol)) was used as the starting material. The number average molecular weight of the polymethylsilazane thus obtained was measured by GPC (developing liquid: $CHCl_3$) and was found to be 1400 in terms of polystyrene. In the IR (infrared absorption) spectrum of the polymethylsilazane, absorption attributable to N-H was observed at wavenumbers (cm^{-1}) 3350 and around 1200; absorption attributable to Si-C was observed at ~~12900~~ 2900 and 1250; and absorption attributable to Si-N-Si was observed at 1020 to 820.